Synthesis and molecular structures of *N*,*N*-dimethylhydroxylamino-trichlorosilane and -germane †

Udo Losehand,^a Norbert W. Mitzel^{*a} and David W. H. Rankin^b

^a Anorganisch-chemisches Institut, Technische Universität München, Lichtenbergstraße 4, 85747 Garching, Germany. E-mail: N.Mitzel@lrz.tum.de

^b Department of Chemistry, University of Edinburgh, West Mains Road, Edinburgh, UK EH9 3JJ

Received 18th August 1999, Accepted 13th October 1999



Published on 01 January 1999. Downloaded on 27/10/2014 08:17:48.

The compounds Cl₃SiONMe₂ and Cl₃GeONMe₂ have been prepared by reacting HONMe₂ with SiCl₄ and GeCl₄, respectively, in the presence of the auxiliary base 2,6-dimethylpyridine. Their identity was proven by gas-phase IR and solution NMR spectroscopy of the nuclei ¹H, ¹³C, ¹⁵N, ¹⁷O, ²⁹Si, by mass spectrometry and elemental analyses. The solid-state structure of Cl₃SiONMe₂ was determined by low-temperature X-ray crystallography. The molecular structures of Cl₃SiONMe₂ and Cl₃GeONMe₂ in the gas phase have been determined by analysis of electron diffraction data augmented by restraints derived from *ab initio* calculations (MP2/6-31G*). The molecules adopt *C*_s symmetry. Important gas-phase geometry parameter values for Cl₃SiONMe₂ are: Si–O 1.623(3), Si–Cl_{in-plane} 2.022(4), Si–Cl_{out-of-plane} 2.024(2), O–N 1.479(6) Å, Si–O–N 105.6(8), O–Si–Cl_{in-plane} 104.2(3), O–Si–Cl_{out-of-plane} 113.7(2)°, for Cl₃GeONMe₂: Ge–O 1.759(6), Ge–Cl_{in-plane} 2.104(4), Ge–Cl_{out-of-plane} 2.106(2), O–N 1.484(9) Å, Ge–O–N 104.0(11), O–Ge–Cl_{in-plane} 108.9(20), O–Ge–Cl_{out-of-plane} 111.6(12)°. The structural data are interpreted in terms of weak attractive interactions between the nitrogen donor and the silicon/germanium acceptor atoms. The results are discussed in comparison with other structural data from the literature: the donor–acceptor interaction in Cl₃SiONMe₂ is weaker than those in H₃SiONMe₂ or ClH₂SiONMe₂, but stronger than that in Me₃SiONMe₂.

Introduction

Silanes and germanes reveal Lewis acidic character depending on the nature of their substituents. The hypervalent base adducts have been intensively investigated¹ and some of them are of pharmaceutical interest.² Compounds with intramolecular donor–acceptor bonds form an important subset, and the best known class of compounds in this respect is the silatranes.³ Driving the intramolecular donor–acceptor bond formation to the extreme of only one linker atom between donor and acceptor, three-membered rings can be formed or, as an alternative, oligomerisation can occur to give six-membered or larger ring systems.

We have studied internal donor-acceptor bond formation between E and N in E–O–N fragments (E = Si, Ge, Sn) and found a wide spectrum of strength of such interactions ranging from predictably weak ones *e.g.* in Me₃SiONMe₂ [Si–N: 2.566(8) Å, Si–O–N: 107.9(6)°]⁴ and its germanium analogue, through medium strength interactions *e.g.* in H₂Si(ONMe₂)₂ [Si–N: 2.32 Å, Si–O–N: 95°],⁵ to strong interactions as in the solid state of ClH₂SiONMe₂ [Si–N: 2.028(1) Å, Si–O–N: 79.7(1)°].⁶ In none of these compounds do we observe aggregation to six-membered ring systems, but instead we find a preference for formation of three-membered rings with one weak bond, which may be described as a donor–acceptor interaction with a large electrostatic contribution. The determination of interactions of this type is important to understand specific reactivity of Si–O–N compounds, such as their rearrangements into O–N–Si units,⁷ the use of catalytic amounts of R_2NOH in the alcoholysis reaction of Si–H functions⁸ (also known in a stoichiometric version)⁹ or their use as so-called cold-curing catalysts in silicone polymer synthesis.¹⁰

The principal concept of attractive interactions between geminal centres can be seen in a more general context. For example, interactions of this type have also been postulated for E–C–N linkages (E = Si, Ge, Sn; e.g. in $Me_3SnCH_2NMe_2$), and were used to explain the unusually low basicities of such amines (also named the α -effect).¹¹ However, they could not be proved on the basis of experimental structure determination to date.¹² Other examples from the literature in p-block element chemis try include the compounds $(F_3C)_2BCPh_2NMe_2$, RN=C{Al[CH- $(SiMe_3)_2]_2$ and $(Me_3Si)_2C=N-N\{Al[CH(SiMe_3)_2]\}_2$ with B-C-N,³ Al–C=N⁴ and Al–N–N⁵ linkages forming three-membered ring systems in the solid state. In contrast to the limited number of examples of β -donor interactions in p-block chemistry, such a bonding situation is much more common in transition metal compounds like Ti(ONR₂)₄.¹³ In these cases this type of bonding is also described as η^2 -coordination.

For the bonding situation in Si–O–N units we know that the nucleophilic character of the nitrogen centre is of crucial importance, as has been shown in two recent studies of compounds with reduced basicity at nitrogen: Me₃SiON(CF₃)₂¹⁴ and (Mes)F₂SiON(SiMe₃)₂.¹⁵ We now wanted to evaluate the importance of backbonding from substituents to the acceptor atoms in Si–O–N and Ge–O–N compounds. In comparison to ClH₂SiONMe₂, with its exceptionally strong Si···N interaction, we aimed to prepare and study compounds with a larger number of Cl substituents at Si and Ge. Here we report on the synthesis of Cl₃SiONMe₂ and Cl₃GeONMe₂, and studies of their spectroscopic and structural properties.

J. Chem. Soc., Dalton Trans., 1999, 4291–4297 4291

 $[\]dagger$ Dedicated to Professor H. Schmidbaur on the occasion of his $65^{\rm th}$ birthday.

Supplementary data available: rotatable 3-D crystal structure diagram in CHIME format. See http://www.rsc.org/suppdata/dt/1999/4291/

Also available: correlation matrix elements for Cl_3EONMe_2 (E = Si, Ge). For direct electronic access see http://www.rsc.org/suppdata/dt/ 1999/4291/, otherwise available from BLDSC (No. SUP 57668, 2 pp.) or the RSC Library. See Instructions for Authors, 1999, Issue 1 (http:// www.rsc.org/dalton).

 Table 1
 NMR chemical shifts (ppm) of different O-silylated and O-germylated hydroxylamines

Compound	$\delta^{29} { m Si}$	δ^{15} N	$\delta^{17}\mathrm{O}$
Cl ₃ SiONMe ₂	-42.4	-229.4	161
Cl ₃ GeONMe ₂		-226.7	187
Me ₃ SiONMe ₂	-17.8	-247.8	-13
Me ₃ GeONMe ₂	-40.0	-250.8	146
H ₃ SiONMe ₂		-234.0	112

Results and discussion

Synthesis and characterisation of $Cl_3SiONMe_2$ and $Cl_3GeONMe_2$

The compounds $Cl_3SiONMe_2$ and $Cl_3GeONMe_2$ were prepared by the reaction of *N*,*N*-dimethylhydroxylamine and the corresponding Group 14 tetrachloride in pentane in the presence of 2,6-dimethylpyridine as a non-coordinating hydrogen chloride acceptor.

$$\begin{split} \text{ECl}_4 + \text{HONMe}_2 + 2,& 6\text{-Me}_2\text{C}_5\text{H}_3\text{N} \longrightarrow \\ \text{Cl}_3\text{EONMe}_2 + 2,& 6\text{-Me}_2\text{C}_5\text{H}_3\text{N}\text{\cdot}\text{HCl}, \text{E} = \text{Si}, \text{Ge} \end{split}$$

They were isolated as colourless liquids by fractionation through a series of cold traps. Both Cl₃SiONMe₂ and Cl₃-GeONMe₂ are extremely sensitive to moist air. Cl₃GeONMe₂ is thermally unstable and decomposes rapidly at ambient temperature to give GeCl₄ and the thermodynamically favoured Cl₂Ge(ONMe₂)₂. The chemical properties and molecular structure of Cl₂Ge(ONMe₂)₂ have been described elsewhere.¹⁶

$$2 \operatorname{Cl}_3\operatorname{GeONMe}_2 \longrightarrow \operatorname{GeCl}_4 + \operatorname{Cl}_2\operatorname{Ge}(\operatorname{ONMe}_2)_2$$

The identity of $Cl_3SiONMe_2$ and $Cl_3GeONMe_2$ was proven by NMR spectroscopy (¹H, ¹³C, ¹⁵N, ¹⁷O, and ²⁹Si for Cl_3 -SiONMe₂) and gas-phase IR spectroscopy. Owing to the high air sensitivity and thermal instability of $Cl_3GeONMe_2$, results from mass spectrometry and elemental analysis appeared only to be satisfactory in the case of $Cl_3SiONMe_2$.

Table 1 contains important NMR data for Cl₃SiONMe₂ and Cl₃GeONMe₂. The electronegative chlorine substituents in Cl₃SiONMe₂ lead to a shift of the ²⁹Si NMR signal to low frequency (δ -42.4), compared to the hydrogenated and methylated species H₃SiONMe₂ (δ -40.0) and Me₃SiONMe₂ (δ -17.8), respectively. The ¹⁵N NMR resonances of Cl₃SiONMe₂ (δ -229.4) and Cl₃GeONMe₂ (δ -226.7) are shifted about 20 ppm to high frequency relative to Me₃-SiONMe₂ (δ -247.8) and Me₃GeONMe₂ (δ -250.8), which may indicate a more intense interaction with the acceptor atoms silicon and germanium, respectively. The similarity in the chemical shifts gives further evidence of the similar electronic nature of the nitrogen atoms in Cl₃SiONMe₂ and Cl₃GeONMe₂.

In contrast to the extremely different ¹⁷O NMR chemical shifts of the methylated compounds Me₃SiONMe₂ and Me₃-GeONMe₂ at δ -13 and 146, the ¹⁷O NMR resonances of Cl₃SiONMe₂ and Cl₃GeONMe₂ appear at similar chemical shifts (δ 161 and 187) and are the highest chemical shifts obtained for *O*-silylated and *O*-germylated hydroxylamines.

Crystal structure determination

In order to compare molecular geometries derived from gasphase electron diffraction with solid-state geometries a single crystal of $Cl_3SiONMe_2$ was grown directly from the melt by *in situ* methods. Attempts to perform an analogous experiment for $Cl_3GeONMe_2$ failed due to problems with crystallisation. $Cl_3SiONMe_2$ crystallises with two independent molecules in the unit cell. There are no intermolecular contacts which would normally be regarded as significant. Important geometrical

Table 2 Important crystal structure parameter values (distances/Å, angles/°) for the two independent molecules of $Cl_3SiONMe_2$ in the unit cell

Parameter	Molecule 1	Molecule 2	
Si–O	1.618(2)	1.622(2)	
Si-Cl4	2.018(1)	2.018(1)	
Si-Cl5	2.015(1)	2.022(1)	
Si-Cl6	2.013(1)	2.018(1)	
O–N	1.491(2)	1.493(2)	
N–C7	1.462(4)	1.461(3)	
N–C8	1.455(4)	1.457(3)	
Si-O-N	103.4(1)	102.6(1)	
O-Si-Cl4	104.2(1)	104.3(1)	
O-Si-C15	113.5(1)	113.3(1)	
O-Si-Cl6	113.3(1)	113.5(1)	
O-N-C7	104.2(2)	104.7(2)	
O-N-C8	104.5(2)	104.7(2)	

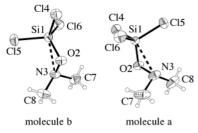


Fig. 1 Crystal structure of $Cl_3SiONMe_2$ as determined by low-temperature crystallography with numbering scheme for the two independent molecules in the asymmetric unit. The molecules are shown in their relative orientation towards each other in the crystal lattice.

parameter values are listed in Table 2. Both molecules show a distorted tetrahedral geometry at the silicon centre due to an intramolecular donor–acceptor interaction between silicon and nitrogen (Fig. 1). These Si \cdots N β -donor–acceptor interactions lead to small Si \cdots N distances of 2.441(2) and 2.432(2) Å and markedly compressed Si–O–N angles of 103.4(1) and 102.6(1)°. Surprisingly, the Si \cdots N β -donor–acceptor interactions in this case and in H₃SiONMe₂ [Si–O–N 102.6(1)°, Si \cdots N 2.456(1) Å] are very similar, whereas in ClH₂SiONMe₂ the Si–O–N angle is 24° less and the Si \cdots N distance is 0.41 Å shorter. Moreover, this is despite the fact that H₃SiONMe₂ and ClH₂SiONMe₂ are both compounds with a less electrophilic silicon centre, or in other words with a less positive charge at the silicon atom, which could be expected to lead to a stronger electrostatic attraction between Si and N atoms in Cl₃SiONMe₂.

The N–O bond length [1.492(ave) Å] is significantly elongated with respect to the non-silylated HONMe₂ [1.452(ave) Å], but of the same length as in ClH₂SiONMe₂ [1.490(1) Å]. A marked distortion of the coordination sphere of silicon is obvious from the different O–Si–Cl angles, with the angle in the (pseudo-)plane of symmetry being about 104°, while the other two are widened to more than 113° in both independent molecules. This and the other parameter values justify the silicon atom in Cl₃SiONMe₂ being regarded as (4 + 1)coordinate.

Gas-phase structure determination

The high volatility of both Cl₃SiONMe₂ and Cl₃GeONMe₂ allowed the determination of their molecular structures in the gas phase by means of electron diffraction. In supporting the refinement by restraints derived from *ab initio* geometry optimisations the usual limitations of gas-phase structure refinements can be overcome. This procedure is called the SARACEN method¹⁷ and introduces an elaborate combination of Bartell's method of predicating values¹⁸ and Schäfer's MOCED method.¹⁹

Table 3 Geometrical parameter values and restraints for the GED refinements of $Cl_3SiONMe_2$ and $Cl_3GeONMe_2$. The parameter values from the *ab initio* calculations (MP2/6-31G*) are listed for comparison. Distances are given in Å, angles and torsion angles in °

		Cl ₃ SiONMe	22		Cl ₃ GeONMe ₂				
No.	Parameter	Value	Restraint	MP2/6-31G*	Value	Restraint	MP2/6-31G*		
<i>p</i> 1	E-Cl4	2.022(4)		2.034	2.104(4)		2.129		
p2	EC15/6	2.024(2)	p2 - p1 = 0.001(5)	2.035	2.106(2)	p2 - p1 = 0.001(5)	2.130		
p3	E–O	1.623(3)		1.663	1.759(6)		1.789		
p4	O–N	1.479(6)		1.492	1.484(9)		1.500		
p5	N–C7	1.445(4)	p5 - p4 = 0.031(10)	1.461	1.447(7)	p5 - p4 = 0.040(10)	1.460		
<i>p</i> 6	C7–H9	1.142(9)		1.089	1.095(21)		1.090		
p7	C7-H10	1.146(9)	p7 - p6 = 0.004(5)	1.093	1.098(22)	p7 - p6 = 0.003(5)	1.093		
<i>p</i> 8	C7-H11	1.150(9)	p7 - p6 = 0.008(5)	1.097	1.101(22)	p7 - p6 = 0.007(5)	1.097		
p9	O-E-Cl4	104.2(3)		104.1	108.9(20)		108.9		
p10	E-O-N	105.6(8)		100.4	104.0(11)		95.6		
p11	O–N–C	107.0(5)	$2 \times p11 + p12 = 320.6(30)$	104.5	106.3(9)	$2 \times p11 + p12 = 320.8(30)$	104.5		
p12	C7–N–C8	114.9(7)	p12 - p11 = 7.10(10)	111.6	114.1(11)	p12 - p11 = 7.4 (10)	111.9		
p13	O-E-C15/6	113.7(2)	• • • • •	113.0	111.6(12)	• • • • •	112.9		
p14	N-C7-H9	107.9(9)	p14 = 108.9(10)	108.9	108.1(10)	p14 = 108.9(10)	108.9		
p15	N-C7-H10	106.5(10)	p15 - p14 = 1.5(5)	107.4	106.9(11)	p15 - p14 = 1.2(5)	107.7		
p16	N-C7-H11	110.2(10)	p16 - p14 = 2.5(5)	111.4	110.5(11)	p16 - p14 = 2.4(5)	111.2		
p17	$\tau C-N-C-H9$	-198.1(31)		-176.8	-197.5(89)		-177.2		
p18	τ C–N–C–H10	41.9(27)	p18 - p17 = 241.9(30)	65.1	44.5(89)	p18 - p17 = 241.8(30)	64.6		
p19	τC-N-C-H11	-76.6(32)	p19 - p17 = 121.4(30)	-55.4	-77.0(90)	p19 - p17 = 121.2(30)	-56.0		
p20	$\tau N-O-E-C15$	60.6(5)	· · ·	62.5	58.9(37)		62.1		

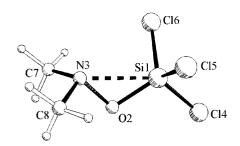


Fig. 2 Molecular structure of $Cl_3SiONMe_2$ in the gas phase as determined by electron diffraction with numbering scheme. The structure of $Cl_3GeONMe_2$ is similar, the numbering scheme analogous.

The molecular framework and atom numbering scheme for Cl₃SiONMe₂ and Cl₃GeONMe₂ are shown in Fig. 2. The mathematical model for the least squares refinement of both compounds was defined in C_s symmetry, with six bond lengths: E-O, E-Cl4, E-Cl5, O-N, N-C and one C-H distance for the methyl groups bound to nitrogen. The differences between the C-H distances within these groups were restrained to the values obtained from ab initio calculations at the MP2/6-31G* level of theory. Parameters for refinement were the angles O-E-Cl4, O-E-Cl5/6, E-O-N, O-N-C, C-N-C, and the angles N-C-H as well as the torsion angles τ NOEC15 and τ CNCH, whereby the differences between parameters for the different hydrogen atoms were again restrained to calculated values. In all 20 geometry parameters were refined under the action of 10 restraints defining the differences of parameters of similar nature or absolute values in the case of hydrogen-defining parameters. The parameter and restraint definitions are given in Table 3; the uncertainties are based on experience with the reliability of these calculations. Also 21 amplitudes of vibration were refined concurrently, representing all amplitudes belonging to pairs of scatterers with a contribution of more than 5% of the scattering of the E-Cl pair. Most of these amplitudes were subject to restraints, either absolute or ratios between related amplitudes, with the values taken from a force field computed at the MP2/6-31G* level of theory and transformed into amplitudes by means of the program ASYM4013 after scaling it by an overall factor of 0.93, which is an established constant in our laboratories. These amplitudes and restraints are given in Table 4. The quality of the refinement can be assessed from the residuals in the molecular scattering curves (Fig. 3) and the radial distribution curves (Fig. 4). The final R factors

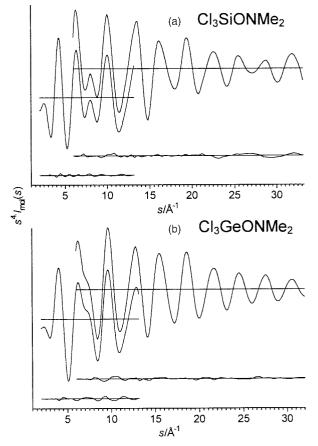


Fig. 3 Experimental molecular scattering intensity and final difference curves (*vs.* model) as obtained by electron diffraction of (a) gaseous $Cl_3SiONMe_2$ and (b) gaseous $Cl_3GeONMe_2$ (including the contribution of GeCl₄).

were 0.053 and 0.052 for $Cl_3SiONMe_2$ and $Cl_3GeONMe_2$. The gas-phase structure of $Cl_3GeONMe_2$ was obtained from a mixture of the compound with GeCl₄, and the scattering contribution of GeCl₄ was treated by including its known gas-phase geometry in the model. The ratio $Cl_3GeONMe_2:GeCl_4$ was found to be 52:48% by variation of the composition parameter in the refinement and an uncertainty of ±5% was estimated by a Hamilton test at the 95% confidence level. Variation of the

 $\label{eq:compounds} \begin{array}{l} \textbf{Table 4} & Distances, amplitudes of vibration and restraints for the GED refinements of the compounds Cl_3SiONMe_2 and Cl_3GeONMe_2. Distances and amplitudes are given in Å \\ \end{array}$

		Cl ₃ SiONMe ₂			Cl ₃ GeONMe ₂		
No.	Atom pair	Distance	Amplitude	Restraint	Distance	Amplitude	Restraint
<i>d</i> 1	E-Cl4	2.022(4)	0.047(2)		2.104(4)	0.043(3)	
<i>d</i> 2	EC15	2.024(2)	0.047(1)	u2/u1 = 0.996(50)	2.106(2)	0.043(3)	u2/u1 = 0.998(50)
<i>d</i> 3	E-O2	1.623(3)	0.044(4)	u3/u1 = 0.949(95)	1.759(6)	0.040(3)	u3/u1 = 0.917(46)
d4	O2–N3	1.479(6)	0.049(4)		1.484(9)	0.055(5)	0.054(54)
d5	N3-C7	1.445(4)	0.045(4)	u5/u4 = 0.928(46)	1.447(7)	0.050(5)	u5/u4 = 0.908(45)
<i>d</i> 6	C7 • • • H9	1.142(9)	0.083(6)	0.078(8)	1.095(22)	0.081(7)	0.077(8)
d7	C7 · · · H10	1.146(9)	0.084(7)	u7/u6 = 1.005(50)	1.098(22)	0.081(8)	u7/u6 = 1.005(50)
<i>d</i> 8	C7 · · · H11	1.150(9)	0.085(7)	u8/u6 = 1.014(51)	1.101(22)	0.082(9)	u8/u6 = 1.014(51)
<i>d</i> 9	$C14 \cdots C15$	3.309(8)	0.076(7)		3.440(72)	0.107(32)	(,)
<i>d</i> 10	$C15 \cdots C16$	3.228(18)	0.076(9)	u10/u9 = 0.998(50)	3.355(153)	0.107(32)	u10/u9 = 1.001(50)
<i>d</i> 11	$Cl4 \cdots O2$	2.886(5)	0.074(7)		3.150(40)	0.096(10)	0.102(10)
d12	$C14 \cdots N3$	4.218(9)	0.098(9)		4.429(25)	0.109(10)	0.104(10)
d13	$Cl4 \cdots C7$	5.018(9)	0.151(11)		5.245(31)	0.145(12)	0.137(14)
d14	$C15 \cdots O2$	3.061(3)	0.072(6)	u14/u11 = 0.978(49)	3.202(23)	0.095(9)	0.099(10)
d15	$C15 \cdots N3$	3.302(12)	0.168(13)	0.161(16)	3.372(27)	0.160(16)	0.156(16)
d16	$C15 \cdots C7$	4.623(11)	0.139(9)		4.699(33)	0.155(15)	0.168(17)
d17	$C15 \cdots C8$	3.675(18)	0.216(17)	0.219(32)	3.733(37)	0.223(21)	0.216(22)
d18	$E \cdots N3$	2.473(12)	0.131(10)		2.562(17)	0.098(11)	0.117(12)
d19	$E \cdots C7$	3.445(10)	0.131(11)	0.124(12)	3.537(17)	0.130(11)	0.123(12)
d20	$02 \cdots C7$	2.351(8)	0.075(6)	u20/u18 = 0.571(57)	2.346(15)	0.080(7)	0.072(7)
d21	$C7 \cdots C8$	2.437(12)	0.075(9)	u21/u18 = 0.577(58)	2.428(18)	0.069(7)	0.069(7)
d22	$C14 \cdots H9$	4.601(27)	0.241	(fixed)	4.836(49)	0.246	(fixed)
d23	$Cl4 \cdots H10$	5.449(42)	0.153	(fixed)	5.652(142)	0.164	(fixed)
d24	$C14 \cdots H11$	5.980(25)	0.240	(fixed)	6.144(64)	0.243	(fixed)
d25	C15 · · · H9	4.772(22)	0.214	(fixed)	4.855(51)	0.215	(fixed)
d26	C15 · · · H10	5.343(22)	0.255	(fixed)	5.388(39)	0.260	(fixed)
d27	Cl5 · · · H11	5.116(32)	0.166	(fixed)	5.150(79)	0.169	(fixed)
d28	Cl6 · · · H9	3.068(38)	0.284	(fixed)	3.144(89)	0.282	(fixed)
d 29	$Cl6\cdots H10$	4.664(31)	0.311	(fixed)	4.671(79)	0.318	(fixed)
d30	$Cl6 \cdots H11$	4.125(57)	0.241	(fixed)	4.129(149)	0.239	(fixed)

 $Cl_3GeONMe_2$: GeCl₄ ratio about the optimised value in this range did not affect the geometric parameters of $Cl_3GeONMe_2$ significantly.

Cl₃SiONMe₂ and Cl₃GeONMe₂ adopt similar molecular structures in the vapour. Each of the compounds shows a compressed E–O–N angle, 105.6(8)° for Cl₃SiONMe₂ and 104.0(11)° for Cl₃GeONMe₂, which leads to short E····N distances [E = Si: 2.473(12) Å, E = Ge: 2.562(17) Å]. The N \rightarrow E donor–acceptor interaction results in a distortion of the tetrahedral coordination geometry, which is more pronounced in Cl₃SiONMe₂ [O–Si–Cl angles 104.2(3) and 113.7(2)°] than in Cl₃GeONMe₂ [O–Ge–Cl angles 108.9(20) and 111.6(12)°]. Angles and distances of relevance are given in Table 3.

Comparison of the results derived from gas-phase electron diffraction and X-ray diffraction of a single crystal of Cl₃-SiONMe₂ shows that both molecular structures are similar. The distortion of the tetrahedral coordination geometry at the silicon centre is, within experimental errors, the same for both gas-phase and crystal structures. Cl₃SiONMe₂ adopts slightly smaller Si–O–N angles in the crystal than in the vapour. This was expected with respect to the known structure of the *anti*-conformer of ClH₂SiONMe₂ [Si–O–N: gas phase 87.1(9)°; crystal lattice 79.1(1)°].⁶ The compression of the Si–O–N angle in the solid state is explained by the increase of the molecular dipole moment due to the regular alignment of the molecules in the crystal lattice.

Ab initio calculations at the MP2(fc)/6-31G* level of theory overestimate the strength of the Si····N interaction: Cl₃-SiONMe₂ is predicted to have a significantly smaller E–O–N angle (100.4°), implying a stronger donor–acceptor interaction than found by experiment. This overestimation of the strength of the E ···N β-donor interaction is even more pronounced for Cl₃GeONMe₂, for which the Ge–O–N angle is computed 8° smaller (95.6°) than the experimental value of 104.0(11)° and the coordination tetrahedron at the germanium centre is less distorted than anticipated by theory (MP2/6-31G*). It is known from earlier comparison of experiments with theory that an improvement in the basis set leads to better values, but so far we have not observed such large deviations. A summary of theoretical and experimental bond lengths and angles is given in Table 3.

In order to improve understanding of the bonding situation in the title compounds, it is worth comparing them with other compounds containing X₃SiO linkages. Selected parameter values for reference compounds are given in Table 5. The Si-O bond in Cl₃SiONMe₂ [1.632(3) Å] is longer than in Cl₃SiOSiCl₃ $[1.592(10) \text{ Å}]^{20}$ or the fluorine analogue $F_3SiOSiF_3$ [1.580(25)Å].²¹ This is consistent with the much narrower valence angle at oxygen in Cl₃SiONMe₂ [105.6(8)°] as compared to these disiloxanes [146(4) and 155.7(20)°], as the strength of a Si-O bond is related to a contribution of the oxygen lone pairs of electrons, which is more correlated with the width of the angle at oxygen. However, compounds without electronegative substituents at silicon have longer Si-O bonds, as is the case in H₃SiOSiH₃ and H₃SiOCH₃ (see Table 5). The variation in the Si-O-X angle from Si-O-Si to Si-O-C to Si-O-N angle is impressive and illustrates the importance of interactions between geminal atoms, which is repulsive in Si-O-Si, about neutral in Si-O-C and attractive in Si-O-N units.

We also wanted to compare our new experimental results with data for related Group 14 hydroxylamino compounds. For this purpose we prepared Table 6, which contains a collection of geometrical data and the corresponding values of the sums of Bartell's one angle radii [these radii define the (non-bonded) distance between geminal atoms, *i.e.* the A ··· C distance in an A–B–C unit enclosing one angle],²² giving an estimate of the non-bonded distance between two geminal atoms bound to a common centre. The table shows that, depending on the substitution pattern, it is possible to achieve an E ··· N distance in E–O–N units which is identical to the sum of Bartell's radii indicating the absence of any attractive interaction, as in MesF₂SiON(SiMe₃)₂. However, it is also possible to achieve

Table 5 Important gas-phase geometrical parameter values (distances/Å, angles/°) for Cl₃SiONMe₂, Cl₃GeONMe₂ and other E–O–E and E–O–C reference compounds (GED values all r_a)

Compound	E–O	E–O–X
Cl ₃ SiONMe ₂	1.623(3)	105.6(8)
Cl ₃ SiOSiCl ₃	1.592(10)	146(4)
F ₃ SiOSiF ₃	1.580(25)	155.7(20)
F ₃ SiOCH ₃ ³¹	1.580(assumed)	131.4(32)
H ₃ SiOSiH ₃	1.634(2)	144.1(8)
H ₃ SiOCH ₃	1.640(3)	120.6(10)
Cl ₃ GeONMe ₂	1.759(6)	104.0(11)
H ₃ GeOGeH ₃	1.766(4)	126.5(3)

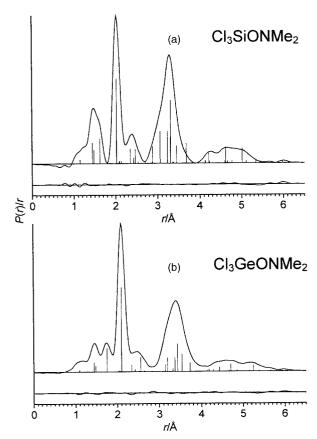


Fig. 4 Radial distribution and difference curve for the electron diffraction refinement of (a) Cl₃SiONMe₂ and (b) Cl₃GeONMe₂ (with the contribution of GeCl₄ subtracted). Before Fourier inversion the data were multiplied by $s \exp[(-0.002 \ s^2)/(Z_E - f_E)(Z_{CI} - f_{CI})]$, E = Si, Ge. Vertical lines indicate atom pairs with their height being proportional to their scattering contribution.

 $E \cdots N$ distances almost as short as the sum of the covalent radii of E and N, as is found in solid ClH₂SiONMe₂.

In Table 6 we see that the Si–O–N and Ge–O–N angles of Cl₃SiONMe₂ and Cl₃GeONMe₂ are in the same range as those of Me₃SiONMe₂ and Me₃GeONMe₂, the latter two having only marginally wider angles and slightly longer $E \cdots N$ distances. One might expect that the electrophilicity of the Cl₃Si and Cl₃Ge groups would lead to much smaller $E \cdots N$ distances associated with smaller Si–O–N and Ge–O–N angles. However, even in H₃SiONMe₂ a stronger attraction between Si and N atoms was observed.

Although most of the molecules under consideration here are comparatively small, a number of different effects play important roles in determining the strength of the $E \cdots N$ attractions. These include (i) electrostatic attraction between positively charged E and negatively charged N atoms, (ii) dipole–dipole and dipole–charge interactions, (iii) electron delocalisation of the types lp(N) $\rightarrow \sigma^*(E-X)$ and lp(O) $\rightarrow \sigma^*(E-X)$, (iv) the anglebending potential at the oxygen atom and (v) steric repulsion

Table 6 Important geometrical parameter values (distances/Å, angles/°) for Cl₃SiONMe₂, Cl₃GeONMe₂ and E–O–N reference compounds (ave = averaged value; GED values all r_a)

Compound/method	E-O-N	E····N	Σ Bartell's radii
Cl ₃ SiONMe ₂ /GED Cl ₃ SiONMe ₂ /XRD Cl ₃ GeONMe ₂ /GED Me ₃ SiONMe ₂ /GED Me ₃ GeONMe ₂ /GED Me ₃ SiON(CF ₃) ₂ /GED Me ₅ SiON(CF ₃) ₂ /XRD	105.6(8) 103.0(ave) 104.0(11) 107.9(6) 108.9(7) 102.5(8) 113.4(19) 117.66(11)	2.473(12) 2.437(ave) 2.562(17) 2.566(8) 2.682(11) 2.731(14) 2.66 2.692	2.69 2.69 2.72 2.69 2.72 3.02 2.69 2.69 2.69
ClH ₂ SiONMe ₂ (<i>anti</i>)/XRD ClH ₂ SiONMe ₂ (<i>anti</i>)/GED ClH ₂ SiONMe ₂ (<i>gauche</i>)/GED H ₃ SiONMe ₂ /XRD H ₂ Si(ONMe ₂) ₂ /XRD	79.7(1) 87.1(9) 104.7(11) 102.6 95.2(ave)	2.028(1) 2.160(7) 2.468(25) 2.453 2.318(ave)	2.69 2.69 2.69 2.69 2.69

between the *gauche* substituents at E and the nitrogen substituents (Me).

In Table 7 a number of computational results are compiled including the E–O–N angles, the atomic charges at E, N and O and the shortest contacts between the atoms in silyl and germyl groups on one side and in the nitrogen substituents on the other side. For the compounds listed in this table, the charges on their N and O atoms vary only slightly, which is to be expected, as all compounds contain the same ONMe₂ group. The charge at the acceptor centre E is largely dependent on the nature of the substituents, with F₃SiONMe₂ being the most extreme case with q(Si) = 1.80 e. Although F₃SiONMe₂ is predicted to show the strongest $E \cdots N$ attraction, there is no obvious dependence of the strength of interaction and the charge on the acceptor centre, as Cl₃SiONMe₂ bears a markedly larger charge on silicon but has a larger Si–O–N angle than ClH₂SiONMe₂. This can be used as an argument against purely electrostatic attraction between E and N atoms as an explanation for the effect under investigation.

However, the compounds with the largest negative charge on nitrogen are those with the strongest $E \cdots N$ interactions. This accumulation of negative charge at nitrogen is inconsistent with the picture of a nitrogen centre donating electrons towards the acceptor atom, or as described in terms of natural orbital analysis with $lp(N) \rightarrow \sigma^*(E-X)$ electron delocalisation. However, calculations for aminoboranes also predict the negative charge at the donor atom (nitrogen) to be slightly higher than in the free amine.²³

The shortest distances between the gauche substituent at silicon and gemanium (Cl in the case of Cl₃SiONMe₂, H in the case of anti-ClH₂SiONMe₂) to the hydrogen atoms of the methyl groups at nitrogen should give an indication of the occurrence of repulsive forces between silyl or germyl groups on one side and methyl groups on the other, which would prevent shortening of the $E \cdots N$ distance, despite an attractive interaction between these centres. This could explain the large difference in the Si ···· N distances in Cl₃SiONMe₂ and ClH₂-SiONMe₂. However, the data in Table 7 show that the Cl \cdots H and H... H distances in Cl₃SiONMe₂ and ClH₂SiONMe₂ are considerably larger than the respective sums of van der Waals radii: the experimental value for the shortest Cl · · · H contact in $Cl_3GeONMe_2$ is 3.068(38) Å (the *ab initio* value is 2.994 Å), whereas the sum of the van der Waals radii is 2.80 Å. The repulsion in Cl₃SiONMe₂ could even be less pronounced if the possibility of weak hydrogen bonding between Cl and H is taken into consideration.

It should finally be noted that a more detailed consideration of orbital interaction is consistent with our experimental results. We performed a natural bond orbital analysis (NBO), despite the obvious deviations of theory from the experi-

Table 7 Computed Mulliken charges q (e), Si–O–N angles (°) and non-bonded distances (Å) between the silyl/germyl groups and the methyl units in Cl₃SiONMe₂, Cl₃GeONMe₂ and E–O–N reference compounds. For consistency all values are taken from fully optimised MP2(fc)/6-31G* calculations

Compound	SiON	q(Si/Ge)	$q(\mathbf{N})$	$q(\mathbf{O})$	Shortest co	ntact	Σ v.d.W. radii
Cl ₃ SiONMe ₂	100.4	1.18	-0.30	-0.60	$Cl \cdots H$	3.012	2.8
Cl ₃ GeONMe,	95.6	0.96	-0.26	-0.60	$Cl \cdots H$	2.994	2.8
F ₃ SiONMe ₂	86.5	1.80	-0.36	-0.59	$F \cdots H$	2.65	2.4
CIH,SiONMe, (anti)	88.9	1.06	-0.33	-0.61	$H \cdots H$	2.70	2.0
ClH ₂ SiONMe ₂ (gauche)	102.1	1.04	-0.28	-0.63	$Cl \cdots H$	3.08	2.8
H ₃ SiONMe ₂	99.9	0.92	-0.29	-0.65	$H \cdots H$	2.92	2.0

Table 8 Experimental conditions (camera distances (mm), electron wavelengths (Å), nozzle and sample temperatures (°C)), data ranges and weighting functions (Å⁻¹), correlation parameters, scale factors and final *R* factors for the GED experiments and refinements of the compounds $Cl_3SiONMe_2$ and $Cl_3GeONMe_2$

Compound/ data set	Camera distance	Wavelength	T nozz	T samp	Δs	S _{min}	<i>s</i> ₁	<i>S</i> ₂	S _{max}	Correlation parameter	Scale factor	R_1	R _g
Cl ₃ SiONMe ₂ /1	285.47	0.06016	20	0	0.2	2.0	4.0	11.2	13.2	0.3650	0.850(5)	0.0388	0.0533
Cl ₃ SiONMe ₂ /2	128.08	0.06016	20	0	0.4	6.0	8.0	28.8	33.2	0.4116	0.890(14)	0.0700	
Cl ₃ GeONMe ₂ /1	285.47	0.06016	20	0	0.2	2.0	4.0	11.2	13.2	0.4842	0.840(5)	0.0574	0.0522
$Cl_3GeONMe_2/2$	128.08	0.06016	20	0	0.4	6.0	8.0	30.8	32.4	0.2903	0.850(10)	0.0469	

mentally obtained geometries. These calculations reveal many small contributions to electron delocalisation in these compounds. The most important to mention are those of the type $lp(O) \rightarrow \sigma^*(E-X)$, which are common for Si-O and Ge-O compounds. A comparatively strong remote type of negative hyperconjugation, $lp(N) \rightarrow \sigma^*(E-X)$, as was used to rationalise the nature of bonding in anti-ClH2SiONMe2, with its extremely small Si-O-N angle, is predicted to be present in Cl₃SiONMe₂ and Cl₃GeONMe₂, but in the latter two cases it makes a substantially smaller contribution. Although it is difficult to take all the contributions into concurrent consideration, it might be argued that the significant contributions of the type $lp(Cl) \rightarrow \sigma^*(E-X)$ saturate the electrophilicity of the $\sigma^*(E-X)$ orbital positioned *anti* relative to the nitrogen lone pair, or to describe it in simpler terms, "backbonding" from the chlorine lone pairs to silicon reduces its electrophilic character.

Experimental

General

The experiments were carried out using a standard Schlenk line or a vacuum line with greaseless PTFE stopcocks (Young's taps), which was directly attached to the gas cell of an FTIR spectrometer (Midac Prospect FTIR). All NMR spectra were recorded at 21 °C on a JEOL JNM-LA400 spectrometer in sealed tubes with C_6D_6 as a solvent directly condensed onto the sample from K/Na alloy.

Syntheses

(*N*,*N*-Dimethylhydroxylamino)trichlorosilane. A solution of *N*,*N*-dimethylhydroxylamine (2.4 g, 40 mmol) and 2,6-dimethylpyridine (4.3 g, 40 mmol) in pentane (30 mL) was added dropwise to a solution of silicon tetrachloride (7.1 g, 42 mmol) in pentane (50 mL) at -55 °C. The mixture was slowly warmed to ambient temperature and all volatile products were separated from the remaining hydrochloride by repeated condensation. The product was separated in good yield (7.6 g, 32 mmol, 71%) by condensation through a series of cold traps held at -35, -60 and -196 °C, with the product retained at -60 °C. (*N*,*N*-Dimethylhydroxylamino)trichlorosilane is a colourless liquid (mp -55 °C) and extremely sensitive to moist air. ¹H NMR: δ 2.33 (s, 6H, H₃C). ¹³C NMR: δ 49.2 (qq, ¹ J_{CH} = 136.9 Hz, ³ J_{CNCH} = 5.1 Hz). ¹⁵N NMR: δ -229.4 (sep, ² J_{NCH} = 2.1 Hz). ¹⁷O-{¹H} NMR: δ 161 (s). ²⁹Si NMR: δ -42.4 (s). GC-MS:

 $m/z = 192 [M^+ - 1], 158 [M^+ - Cl], 133 [M^+ - ON(CH_3)_2].$ H₆C₂Cl₃NOSi (194.52 g mol⁻¹) calc.: C, 12.34; H, 3.11; N, 7.20. Found: C, 12.34; H, 3.66; N, 6.52%.

(*N*,*N*-Dimethylhydroxylamino)trichlorogermane. A solution of *N*,*N*-dimethylhydroxylamine (2.7 g, 45 mmol) and 2,6-dimethylpyridine (4.8 g, 45 mmol) in pentane (30 mL) was added dropwise to a solution of germanium tetrachloride (9.6 g, 45 mmol) in pentane (50 mL) at -55 °C. The mixture was slowly warmed to ambient temperature and all volatile products were separated from the remaining hydrochloride by repeated condensation. The product was separated in good yield (6.2 g, 32 mmol, 71%) by condensation through a series of cold traps held at -20, -60 and -196 °C, with the product retained at -60 °C. (*N*,*N*-Dimethylhydroxylamino)trichlorogermane is a colourless liquid, extremely sensitive to moist air and thermally unstable. ¹H NMR: δ 2.28 (s, 6H, H₃C). ¹³C-{¹H} NMR: δ 49.84 (s, CH₃). ¹⁵N-{¹H} NMR: δ -226.7 (s). ¹⁷O-{¹H} NMR: δ 187 (s). IR: 2990, 2870 v(CH), 1144 cm⁻¹.

Crystal structure determination of Cl₃SiONMe₂

A single crystal of Cl₃SiONMe₂ was grown *in situ* by slowly cooling the melt in a sealed capillary below the melting point after generation of a suitable seed crystal. C₂H₆Cl₃NOSi, $M_r = 194.5$, crystal system triclinic, space group $P2_1/c$, Z = 8, a = 11.585(1), b = 7.487(1), c = 19.069(2) Å, $\beta = 98.37(1)^\circ$, V = 1636.4(3) Å³ at 149(2) K, $\mu = 1.184$ mm⁻¹. $2\theta_{max} = 56^\circ$, ω -scan, 3545 independent reflections [$R_{int} = 0.032$]. 187 parameters, $R_1 = 0.0355$ for 3532 reflections with $F_o > 4\sigma(F_o)$ and $wR_2 = 0.1029$ for all 3532 data.

CCDC reference number 186/1696.

See http://www.rsc.org/suppdata/dt/1999/4291/ for crystallographic files in .cif format.

Gas-phase electron diffraction

Electron scattering intensity data for $Cl_3SiONMe_2$ and $Cl_3-GeONMe_2$ were recorded on Kodak Electron Image plates using the Edinburgh electron diffraction apparatus.²⁴ The samples were held at 0 °C and the inlet nozzle at 20 °C during the experiments. Scattering data for benzene were recorded concurrently and used to calibrate the electron wavelength and camera distances. Three exposures were taken at each camera distance. Data were obtained in digital form using the microdensitometer at the Royal Greenwich Observatory at Cambridge.²⁵ The experimental conditions and data ranges are listed in Table 8.

Ab initio calculations

Ab initio molecular orbital calculations were carried out using the Gaussian 98 program.²⁸ Geometry optimisations and vibrational frequency calculations were performed from analytic first and second derivatives at the SCF and MP2 levels of theory. Calculations were undertaken at the SCF level using the standard 3-21G*²⁹ and 6-31G*³⁰ basis sets, while the larger was used for calculations at the MP2 level of theory. NBO calculations were undertaken with the NBO 3.0 facilities built into Gaussian 98.

Acknowledgements

This work was supported by the Bayerisches Staatsministerium für Wissenschaft, Forschung und Kunst (Bayerischer Habilitationsförderpreis 1996 for N. W. M.), the Deutsche Forschungsgemeinschaft, the Fonds der Chemischen Industrie, the Leonhard-Lorenz-Stiftung and EPSRC (Grant No. GR/ K44411). Generous support by Professor H. Schmidbaur (Garching) is gratefully acknowledged.

References

- 1 (a) R. R. Holmes, *Chem. Rev.*, 1990, **90**, 17; (b) C. Chuit, R. J. P. Corriu, C. Reyé and J. C. Young, *Chem. Rev.*, 1993, **93**, 1371.
- 2 R. Tacke, D. Reichel, M. Kropfgans, P. G. Jones, E. Mutschler, J. Gross, X. Hou, M. Waeldbrock and G. Lambrecht, Organometallics, 1995, 14, 251.
- 3 (a) M. G. Voronkov, V. M. Dyakov and S. V. Kirpichenko, J. Organomet. Chem., 1982, 233, 1; (b) M. W. Schmidt, T. L. Windus and M. S. Gordon, J. Am. Chem. Soc., 1995, 117, 7480.
- 4 N. W. Mitzel, U. Losehand and A. Richardson, Organometallics, 1999, 18, 2610.
- 5 N. W. Mitzel and U. Losehand, Angew. Chem., Int. Ed. Engl., 1997, 36, 2807.
- 6 N. W. Mitzel and U. Losehand, J. Am. Chem. Soc., 1998, 120, 7320.
- 7 P. Nowakovski and R. West, J. Am. Chem. Soc., 1976, 98, 5616.
- 8 Y. Hamada and S. Mori, Proceedings of the 29th Organosilicon
- *Symposium*, Evanston, IL, March 1996. 9 R. A. Murphy, *Fr. Pat.*, 1462725, 1966; *Chem. Abstr.*, 1967, **67**, 54258.
- 10 M. G. Voronkov, E. A. Maletina and V. K. Roman, *Heterosiloxanes Vol. 2, Derivatives of Nitrogen and Phosphorus*, Harwood Academic Publishers GmbH, Chur, Switzerland, 1991.
- 11 (a) M. G. Voronkov, V. P. Feshin, V. F. Mironov, S. A. Mikhailyants and T. K. Gar, *Zh. Obshch. Khim.*, 1971, **41**, 2211; (b) M. G. Voronkov, T. V. Kashik, E. Y. Lukevits, E. S. Deriglazova, A. E. Pestunovich and R. Y. Moskovich, *Zh. Obshch. Khim.*, 1974, **44**, 2211.
- 12 N. W. Mitzel, C. Kiener and D. W. H. Rankin, *Organometallics*, 1999, **18**, 3437.

- 13 (a) K. Wieghard, I. Tolksdorf, J. Weiss and W. Swiridoff, Z. Anorg. Allg. Chem., 1982, 490, 182; (b) N. W. Mitzel, S. Parsons, A. J. Blake and D. W. H. Rankin, J. Chem. Soc., Dalton Trans., 1996, 2089.
- 14 T. Hertel, J. Jakob, R. Minkwitz and H. Oberhammer, *Inorg. Chem.*, 1998, **37**, 5092.
- 15 R. Wolfgramm, U. Klingebiel and M. Noltemeyer, Z. Anorg. Allg. Chem., 1998, 624, 856.
- 16 U. Losehand and N. W. Mitzel, Eur. J. Inorg. Chem., 1998, 2023.
- 17 (a) A. J. Blake, P. T. Brain, H. McNab, J. Miller, C. A. Morrison, S. Parsons, D. W. H. Rankin, H. E. Robertson and B. A. Smart, *J. Phys. Chem.*, 1996, **100**, 12280; (b) N. W. Mitzel, B. A. Smart, A. J. Blake, H. E. Robertson and D. W. H. Rankin, *J. Phys. Chem.*, 1996, **100**, 9339.
- 18 L. S. Bartell, D. J. Romenensko and T. C. Wong, Mol. Struct. Diffr. Methods, 1975, 3, 72.
- 19 V. J. Klimkowski, J. D. Ewbank, C. Van Alsenoy, J. N. Scarsdale and L. Schäfer, J. Am. Chem. Soc., 1982, 104, 1476.
- 20 (a) W. Airey, C. Glidewell, A. G. Robiette and G. M. Sheldrick, J. Mol. Struct., 1971, 8, 413; (b) M. Yokoi, Bull. Chem. Soc. Jpn., 1957, 30, 100; (c) K. Yamasaki, A. Kotera, M. Yokoi and Y. Ueda, J. Chem. Phys., 1950, 18, 1414.
- 21 W. Airey, C. Glidewell, D. W. H. Rankin, A. G. Robiette, G. M. Sheldrick and D. W. J. Cruickshank, *Trans. Faraday Soc.*, 1970, 66, 551.
- 22 (a) L. S. Bartell, J. Chem. Phys., 1960, 32, 827; (b) C. Glidewell, Inorg. Chim. Acta, 1975, 12, 219.
- 23 A. Haaland, Angew. Chem., Int. Ed. Engl., 1989, 28, 992.
- 24 C. M. Huntley, G. S. Laurenson and D. W. H. Rankin, J. Chem. Soc., Dalton Trans., 1980, 945.
- 25 J. R. Lewis, P. T. Brain and D. W. H. Rankin, *Spectrum*, 1997, 15, 7.
 26 N. W. Mitzel, P. T. Brain and D. W. H. Rankin, ED96, Version 2.0, 1998. A program developed on the basis of formerly described ED programs: A. S. F. Boyd, G. Laurenson and D. W. H. Rankin, *J. Mol. Struct.*, 1981, 71, 217.
- 27 A. W. Ross, M. Fink and R. Hilderbrandt, *International Tables for X-Ray Crystallography*, ed. A. J. C. Wilson, Kluwer Academic Publishers, Dordrecht, Boston, 1992, vol. C, p. 245.
- 28 Gaussian 98, Revision A.6, M. J. Frisch, G. W. Trucks, H. B. Schlegel, G. E. Scuseria, M. A. Robb, J. R. Cheeseman, V. G. Zakrzewski, J. A. Montgomery, Jr., R. E. Stratmann, J. C. Burant, S. Dapprich, J. M. Millam, A. D. Daniels, K. N. Kudin, M. C. Strain, O. Farkas, J. Tomasi, V. Barone, M. Cossi, R. Cammi, B. Mennucci, C. Pomelli, C. Adamo, S. Clifford, J. Ochterski, G. A. Petersson, P. Y. Ayala, Q. Cui, K. Morokuma, D. K. Malick, A. D. Rabuck, K. Raghavachari, J. B. Foresman, J. Cioslowski, J. V. Ortiz, B. B. Stefanov, G. Liu, A. Liashenko, P. Piskorz, I. Komaromi, R. Gomperts, R. L. Martin, D. J. Fox, T. Keith, M. A. Al-Laham, C. Y. Peng, A. Nanayakkara, C. Gonzalez, M. Challacombe, P. M. W. Gill, B. Johnson, W. Chen, M. W. Wong, J. L. Andres, C. Gonzalez, M. Head-Gordon, E. S. Replogle and J. A. Pople, Gaussian, Inc., Pittsburgh, PA, 1998.
- 29 (a) J. S. Binkley, J. A. Pople and W. J. Hehre, J. Am. Chem. Soc., 1980, 102, 939; (b) M. S. Gordon, J. S. Binkley, J. A. Pople, W. J. Pietro and W. J. Hehre, J. Am. Chem. Soc., 1982, 104, 2797; (c) W. J. Pietro, M. M. Francl, W. J. Hehre, D. J. Defrees, J. A. Pople and J. S. Binkley, J. Am. Chem. Soc., 1982, 104, 5039.
- 30 (a) W. J. Hehre, R. Ditchfield and J. A. Pople, J. Chem. Phys., 1972, 56, 2257; (b) P. C. Hariharan and J. A. Pople, Theor. Chim. Acta, 1973, 28, 213.
- 31 J. D. Odom, E. J. Stampf, Y. S. Li and J. R. Durig, J. Mol. Struct., 1978, 49, 1.

Paper 9/06688H